

N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY					
V _{(BR)DSS} (V)	$r_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ)		
60	0.0055 at V _{GS} = 10 V	90 ^d	78.5		

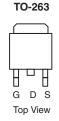
FEATURES

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_q and UIS Tested

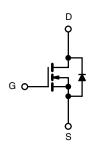


APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- Industrial



Ordering Information: SUM90N06-5m5P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _C = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	60	V		
Gate-Source Voltage	V _{GS}	± 20	V		
Continuous Drain Current (T _{.I} = 175 °C)	T _C = 25 °C	1-	90 ^d		
Continuous Diam Current (1j = 175 C)	T _C = 70 °C	I _D	90 ^d	_	
Pulsed Drain Current	I _{DM}	240	A		
Avalanche Current	I _{AS}	50			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ	
Mariana Barra Birainatina	T _C = 25 °C	В	272 ^b	w	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	$ P_D$ $-$	3.75	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	- 55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.55	C/VV		

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

SUM90N06-5m5P

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage $V_{(BR)D}$		$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V _{DS} = 60 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 150 °C			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	70			Α	
	_	V _{GS} = 10 V, I _D = 20 A		0.0045	0.0055		
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.0072	0.009	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		58		S	
Dynamic ^b				•			
Input Capacitance	C _{iss}			4700		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		620			
Reverse Transfer Capacitance	C _{rss}			250			
Total Gate Charge ^c	Qg			78.5	120		
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		28		nC	
Gate-Drain Charge ^c	Q_{gd}			20.6			
Gate Resistance	R_{g}	f = 1 MHz		1.2	2.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			16	30		
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω		10	20		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D\cong 50$ A, $V_{GEN}=10$ V, $R_g=1$ Ω		25	40	ns	
Fall Time ^c	t _f			8	15		
Source-Drain Diode Ratings and Cha	racteristics T ₀	_C = 25 °C ^b		•			
Continuous Current	I _S				85		
Pulsed Current	I _{SM}				240	Α	
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.83	1.5	V	
Reverse Recovery Time	t _{rr}			62	100	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	$I_F = 75 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		3.8	5.7	Α	
Reverse Recovery Charge	Q _{rr}			118	180	nC	

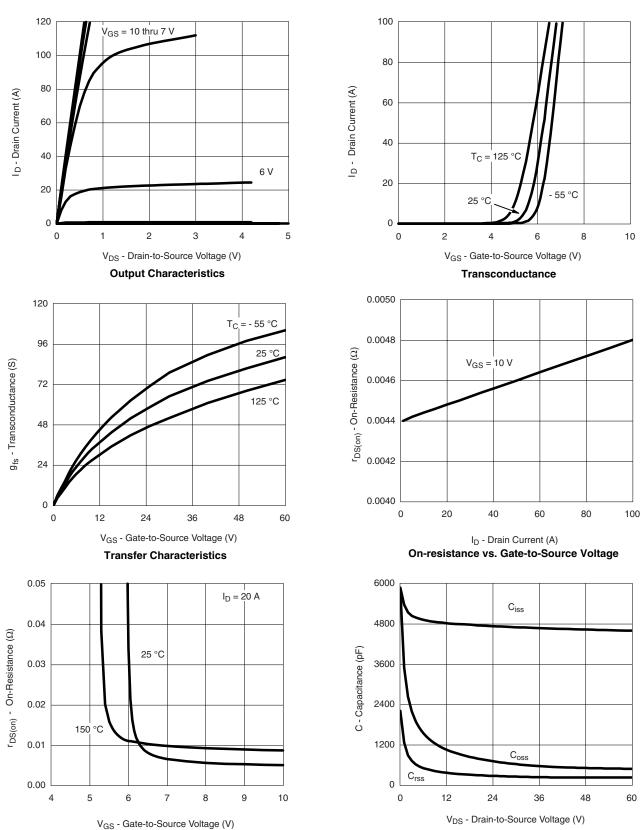
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



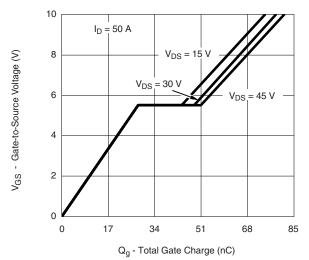
On-Resistance vs. Drain Current

Capacitance

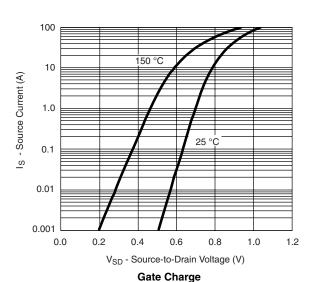
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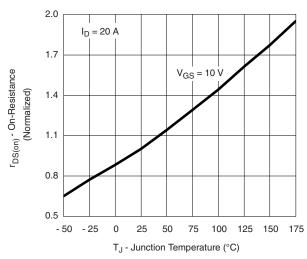
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



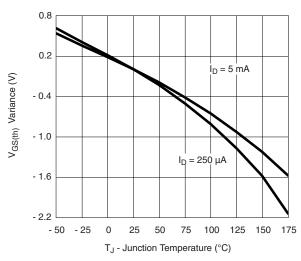
On-Resistance vs. Junction Temperature



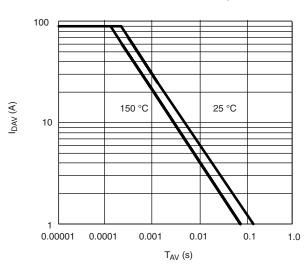
Source-Drain Diode Forward Voltage



Threshold Voltage



On-Resistance vs. Junction Temperature



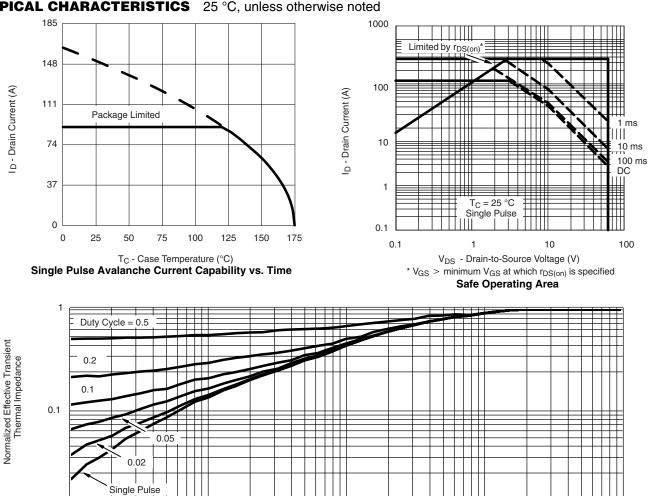
Maximum Drain Current vs. Case Temperature



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

10-3



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

10-2

10⁻¹

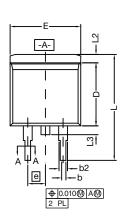
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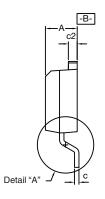
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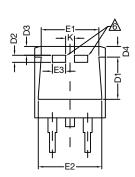
10-4



TO-263 (D²PAK): 3-LEAD

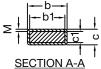








DETAIL A (ROTATED 90°)



= 1	b	<u>.</u>
$\geq \frac{1}{1}$	<i>।।।।।।</i> । ਹ	
c		\Box

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6 This feature is for thick lead.

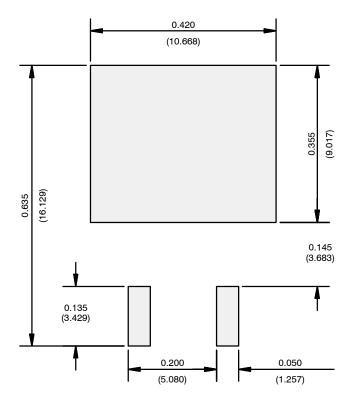
DIM.		INC	HES	MILLIMETERS		
		MIN.	MAX.	MIN.	MAX.	
Α		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
	D3	0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
	Е	0.380	0.410	9.652	10.414	
E1		0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
	E3	0.072	0.078	1.829	1.981	
е		0.100	BSC	2.54 BSC		
K		0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
L4		0.010 BSC		0.254 BSC		
	М	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13						

DWG: 5843





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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